

FOR USE BY ELECTRICIANS OVERSEAS:

最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型 名	社 名	用 途	構 造	最大 定 格 ($T_a=25^{\circ}\text{C}$)					電 気 的 特 性 ($T_a=25^{\circ}\text{C}$)										外 形	備 考	
				V_{CBO} (V)	V_{CEO} (V)	I_C (mA)	P_C (mW)	T_j ($^{\circ}\text{C}$)	I_{CBO} 最大値 (μA)	V_{CE} (V)	直流又はパルス h_{FE} I_C (mA)	バイアス V_{CE} (V)	h_{FE} h_{FE}^*	h_{ie} h_{ie}^* (Ω)	h_{re} h_{re}^* ($\times 10^{-4}$)	h_{oe} h_{oe}^* (μS)	f_{α} f_{α}^* (Mc)	C_{ob} (pF)			$r_{bb'}$ $r_{bb'}(\text{real})^*$ (Ω)
1	2	3	4	5					6	7				8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{cso} MAXIMUM VALUE AND V_{ce} VALUE (CRITERIA FOR MEASURING I_{cso})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{ce} , I_c (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{ce} , I_E (CRITERIA FOR MEASURING h PARAMETERS)

* INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.

- 9 $f_{\alpha b}$ OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_T .
- 10 C_{ob} AND $r_{bb'}$ OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN $r_{bb'}$ COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11 OUTLINE
- 12 REMARKS

: とコンプリ: COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 ($T_a = 25^{\circ}\text{C}$)					電 気 的 特 性 ($T_a = 25^{\circ}\text{C}$)										外形	備 考				
				V_{CBO} (V)	V_{EBO} (V)	I_C (mA)	P_C (mW)	T_j ($^{\circ}\text{C}$)	I_{CBO} 最大値 (μA)	V_{CE} (V)	直流又はパルス h_{FE} V_{CE} (V)	I_C (mA)	V_{CB} (V)	I_E (mA)	h_{fe} h_{fe}^*	h_{ie} h_{ie}^* (Ω)	h_{re} h_{re}^* ($\times 10^{-4}$)	h_{oe} h_{oe}^* (μS)			f_{β} f_T^* (Mc)	C_{ob} (pF)	r_{bb} $r_{bb}(\text{real})^*$ (Ω)	
2SC2112																								
★	"	2113 松下	PA	Si.EP	40	5	1 A	1 W	150	1	20	220	10	50	5	-500			100*	50	3.3k*	222		
	"	2114 東芝	RF.LN	"	15	3	80	225	125	0.1	10	75	3	50	5	-30	$G_{pr} = 9\text{dB}$, $NF = 4\text{dB}$ ($f = 2\text{GHz}$, $V_{CE} = 5\text{V}$, $I_C = 30\text{mA}$)			7000*	1	20*	317	
	"	2115 "	"	"	20	2	30	150	125	1	10	120	5	10	5	-10	$G_{pr} = 9\text{dB}$, $NF = 4\text{dB}$ ($f = 2\text{GHz}$, $V_{CE} = 5\text{V}$, $I_C = 5\text{mA}$)			6500*	0.6	15*	317	
	"	2116 "	"	"	30	3	50	225	125	1	10	80	10	10	10	-5	$G_{pr} = 15\text{dB}$, $NF = 2.5\text{dB}$ ($f = 500\text{MHz}$, $V_{CE} = 10\text{V}$, $I_C = 4\text{mA}$)			3000*	1.2	40*	317	
	"	2117 "	PA	"	35	3.5	800	7.5W ($T_c = 25^{\circ}\text{C}$)	175	1mA	15	>10	5	500					<15			97C	エミッタ・ベース接続	
	"	2118 "	"	"	35	3.5	1.4A	10W ($T_c = 25^{\circ}\text{C}$)	175	1mA	15	>10	5	1 A					<25			97C	エミッタ・ベース接続	
★	"	2119 "	"	Si.E	80	4	4 A	12.5W ($T_c = 25^{\circ}\text{C}$)	150	15	40	50	5	2 A								268		
	"	2120 "	"	Si.EP	30	5	800	600	150	0.1	35	100-320	1	100	5	-10	$P_o = 8\text{W}$ ($f = 175\text{MHz}$, $V_{CE} = 13.5\text{V}$, $P_i = 0.6\text{W}$)						138	2SA950 とコンパリ
	"	2121 "	SW	Si.TMe	750	6	3 A	50W ($T_c = 25^{\circ}\text{C}$)	150	I_{CEX} 500	750	15-60	5	1 A	10	-200			8*	85		102		
	"	2122 "	"	"	800	8	10A	50W ($T_c = 25^{\circ}\text{C}$)	150	I_{CEX} 1mA	800	>15	10	2.5A	10	-100	$t_f < 1\mu\text{S}$			6*	125	102	水平偏向用	
	"	2123 "	"	"	1000	8	12A	50W ($T_c = 25^{\circ}\text{C}$)	150	I_{CEX} 1mA	1000	>5	5	8 A	10	-500	$t_f < 1\mu\text{S}$			6*	125	102	水平偏向用	
★	"	2124 "																						
★	"	2125 東芝	PA	Si.TMe	2200	5	5 A	50W ($T_c = 25^{\circ}\text{C}$)	150	500	2200	25	10	1 A	10	-100			5*	165	10	102		
	"	2126 新電元	SW	Si.T	200	6	3 A	30W ($T_c = 25^{\circ}\text{C}$)	150	250	200	42	3	3 A			$t_{on} < 1\mu\text{S}$, $t_f < 1\mu\text{S}$ $t_{off} < 2\mu\text{S}$						204	
	"	2127 "	"	"	200	6	10A	100W ($T_c = 25^{\circ}\text{C}$)	150	250	200	32	3	10A			$t_{on} < 1\mu\text{S}$, $t_f < 1\mu\text{S}$ $t_{off} < 2\mu\text{S}$						102	
	"	2128 "	"	"	200	6	30A	200W ($T_c = 25^{\circ}\text{C}$)	150	500	200	22	3	30A			$t_{on} < 1\mu\text{S}$, $t_f < 1\mu\text{S}$ $t_{off} < 2\mu\text{S}$						266	
	"	2129 三菱	AF.LN.RF	Si.EP	70	5	100	200	125	0.1	50	250-1200	6	1	6	-1	$V_{NO} < 300\text{mV}$ (10V, 1mA, $R_G = 100\Omega$, $A_v = 80\text{dB}$)			100*	3	45	138B	
	"	2130 "	AF.RF	"	70	5	100	200	125	0.1	50	250-1200	6	1	6	-1			100*	3		138B		
	"	2131 "	PA	"	40	4	600	800	175	100	25	50	10	100			$P_o = 1.6\text{W}$, $\eta = 60\%$ ($f = 500\text{MHz}$, $V_{CE} = 13.5\text{V}$, $P_i = 0.3\text{W}$)						84B	エミッタ・ベース接続
★	"	2132 "	"	"	35	4	9 A	50W ($T_c = 25^{\circ}\text{C}$)	175	1mA	15	50	10	1 A			$P_o = 30\text{W}$, $\eta = 65\%$ ($f = 470\text{MHz}$, $V_{CE} = 13.5\text{V}$, $P_i = 10\text{W}$)						313	MTH004
	"	2133 "	"	"	55	4	5 A	75W ($T_c = 25^{\circ}\text{C}$)	175	2mA	35	50	25	200			$P_o = 34\text{W}$, $\eta = 60\%$ ($f = 220\text{MHz}$, $V_{CE} = 28\text{V}$, $P_i = 4.5\text{W}$)						313	
	"	2134 "	"	"	55	4	10A	120W ($T_c = 25^{\circ}\text{C}$)	175	5mA	35	50	25	200			$P_o = 70\text{W}$, $\eta = 60\%$ ($f = 220\text{MHz}$, $V_{CE} = 28\text{V}$, $P_i = 1212\text{W}$)						313	
	"	2135 ソニー	SW	Si.EPa	4	4	50	140	60	0.001	3	>500	3	1			逆方向 $h_{FE} > 500$ ($V_{CE} = 3\text{V}$, $I_E = -1\text{mA}$)						138D	双方向性
	"	2136 "																						
	"	2137 東芝	SW	Si.TMe	500	6	6 A	80W ($T_c = 25^{\circ}\text{C}$)	150	100	400	>10	5	3 A			$t_{on} < 1\mu\text{S}$, $t_f < 1\mu\text{S}$ $t_{off} < 2\mu\text{S}$						102	
	"	2138 "	"	"	400	6	6 A	80W ($T_c = 25^{\circ}\text{C}$)	150	100	300	20	5	3 A	10	-1A	$t_{on} < 1\mu\text{S}$, $t_f < 1\mu\text{S}$ $t_{off} < 2\mu\text{S}$			6*			102	
	"	2139 "	"	"	500	6	10A	100W ($T_c = 25^{\circ}\text{C}$)	150	100	400	>20	5	5 A			$t_{on} < 2\mu\text{S}$, $t_f < 2\mu\text{S}$ $t_{off} < 4\mu\text{S}$						102	
	"	2140 "	"	"	400	6	10A	100W ($T_c = 25^{\circ}\text{C}$)	150	100	300	20	5	5 A	10	-1A	$t_{on} < 2\mu\text{S}$, $t_f < 2\mu\text{S}$ $t_{off} < 4\mu\text{S}$			6*			102	
	"	2141 ソニー	PA	Si.EPa	140	8	500	950	120	0.2	100	150	2	100	10	-20			50*	15	174B	2SA951 とコンパ		